

Instruction for the Preparation of Manuscript for the Workshop Proceedings

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Abstract

An introduction for preparing manuscripts for the proceedings of the Superconducting SFQ VLSI Workshop (SSV) is given in the present paper. This paper is written in the format to be used for all manuscripts and illustrates the final appearance of the proceedings. It is essential to follow these instructions to both ensure that your manuscript is quickly accepted and to present consistent and professional-looking workshop proceedings publication.

1. Introduction

All papers should be written in English. The title should be followed by the name(s) of the author(s), the institution, and its address. The outline of the paper should be set out using appropriate headings, i.e., Abstract, 1. Introduction, 2. Experimental, 3. Results, 4. Discussion, and 5. Conclusions.

In order to publish the proceedings of papers in time, the manuscript must be submitted online no later than the deadline date. The electric version of the camera-ready manuscript (Word file or PDF file) must be uploaded to the SSV website.

1.1. Length of the Manuscript

All papers should be assigned 2–6 pages.

1.2. Tables and Figures

It is the authors' responsibility to have proper captions, Figures, and Tables mounted at their appropriate places in the text. Ensure that the symbols and letters in the Figures and Tables are large enough. The use of EPS or PDF files for Figures is acceptable for LaTeX file submission.

Please use the same style for Figures and Tables, as shown on the next page.

Table 1 Some Parameters for Al and Nb.

Superconductor	Al	Nb
2Δ (meV)	0.34	3.05
δE (eV@5.9 keV)	1.36	4.9
τ_{QP} (ns)	438	0.15
T_c (K)	1.2	9.2

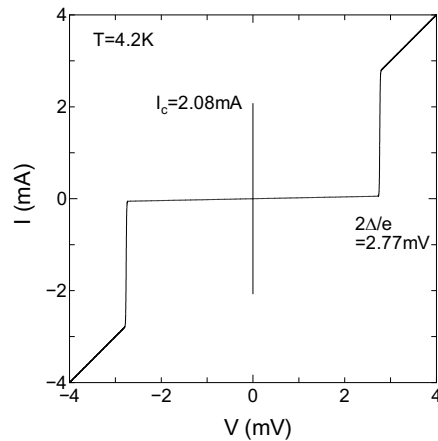


Fig. 1 I-V curve of Nb/AlO_x/Nb junction.

2. References

A list of references should be placed at the end of the paper. Use SINGLE LINE spacing and start each reference on a new line. Please refer to the samples below [1, 2, 3].

Acknowledgment

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References

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